

FORM PTO-1449 (Modified)  INFORMATION DISCLOSURE CITATION IN AN APPLICATION  (Use several sheets if necessary)	Docket No. 378-21-034	Application Number 10/1655,904
	Applicant James D. Parsons	
	Filing Date	Group Art Unit 2878

**U.S. PATENT DOCUMENTS**

## FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

OG	1.	DE VASCONCELOS E A ET AL: "Highly sensitive thermistors based on high-purity polycrystalline cubic silicon carbide" SENSORS AND ACTUATORS A, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, Vol. 83, no. 1-3, May 2000 (2000-05), pages 167-171, XP004198310 ISSN: 0924-4247
	2	DE VASCONCELOS E A ET AL: "Potential of high-purity polycrystalline silicon carbide for thermistor applications" JAPANESE JOURNAL OF APPLIED PHYSICS, PART 1 (REGULAR PAPERS, SHORT NOTES & REVIEW PAPERS), SEPT. 1998, PUBLICATION OFFICE, JAPANESE JOURNAL APPL. PHYS., JAPAN, vol. 37, no. 9A, pages 5078-5079, XP002211060 ISSN: 0021-4922
OG	3	Materials for High Temperature Semiconductor Devices: Committee on Materials for High-Temperature Semiconductor Devices, National Materials Advisory Board, Commission on Engineering and Technical Systems, National Research Council: National Academy Press, Washington, D.C., 1993, pp.68-70.
	4	O. Nennewitz, L. Spiess and V. Breternitz, "Ohmic Contacts to 6H-SiC", Applied Surface Science, Vol. 91, 1995, pages 347-351.
OG	5	J.A. Lely and P.A. Kroeger, "Electrical Properties of Hexagonal SiC Doped with N, B or Al", In Semiconductors and Phosphors, Proceedings of Intl. Colloquium-Partenkirchen, Ed. M. Schoen and H. Welker, New York, Interscience Pub., Inc. 1958, pp. 525-533.
	6	Q.Y. Tong, U. Gosele, C. Yuan, A.J. Stecki & M. Reiche, "Silicon Carbide Wafer Bonding", J. Electrochem Soc., Vol. 142, No. 1, January 1995, pp. 232-236.

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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OG	7	Choyke, W.J., "Optical and Electronic Properties of SiC" NATO ASI Series Vol. "The Physics and Chemistry of Carbides, Nitrides and Borides", Manchester, England, pp. 1-25, 9/18-22, 1999
	8	Spitzer et al., "Infrared Properties of Hexagonal Silicon Carbide", Physical Review, Vo. 113, No. 1, pp. 127-132, January 1, 1959.
OG	9	Electronic Properties Information Center, "Silicon Carbide", Hughes Aircraft Company, June 1965, pp. 9-16.
	10	P.K. Bhattacharya, "Bonding of SiC Slabs for Electro-Mechanical Heat-Sinks in Advanced Packaging Applications", J. Electronics, Vol. 73, No. 1, 1992, pp. 71-81.
OG	11	Westinghouse Astronuclear Laboratory "Silicon Carbide Junction Thermistor", 1965
	12	Jeffrey B. Casady et al, "A Hybrid 6H-Sic temperature Sensor Operational from 25°C to 500°C", IEEE Transactions on Components, Packaging and Manufacturing Technology" - Part A, Vol. 19, No. 3 (September 1996, pp 416-422.

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OG	13	Takashi Nagai and Masahiko Itch, "Sic Thin-Film Thermistors", IEEE Transactions on Industry Applications, Vol. 26, No. 6, November/December 1990, pp. 1139-1143.1
	14	"Electrical Properties of $\beta$ -Sic Heavily Doped with Nitrogen" O. A. Golikova, L.M. Ivanova, A. A. Pletyushin, and V.P. Semenenko, A.A. Balkov Institute of Metallurgy, Academy of Sciences of the USSR, Moscow Institute of Semiconductors, Academy of Sciences of the USSR, Leningrad Translated from Fizika I Tekhnika Poluprovodnikov, Vol. 5, No. 3, pp. 417-420, March 1971, Original article submitted May 26, 1970; revision submitted July 8, 1970.
OG	15	"Galvanomagnetic Effects in n-type Silicon Carbide at Low Temperatures", M.I. Iglytsyn, M. Mirzabaev, V.M. Tuchkovich, E.F. Fedorova, and Yu. V. Shmatsev, A.F. Ioffe Physicotechnical Institute, Academy of Sciences, USSR, Leningrad State Research and Planning Institute for the Rare Metal Industry, Moscow, Translated from fizika Tverdogo Tela, Vol. 6, No. 9, pp. 2673-2682, September, 1964, Original article submitted March 31, 1964
Examiner	<i>Oldi Balk</i>	
	Date Considered	
	03/25/05	
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